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	Application No.	Applicant(s)	
	40/000 000	DAKOHINA MUDTI	IV ET AL
Notice of Allowability	10/632,989 Examin r	DAKSHINA-MURTH	1Y ET AL.
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	David Nhu	2818	<u> </u>
Th MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS nerewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in t) or other appropriate communated; IGHTS. This application is su	his application. If not includ lication will be mailed in due	ed course. THIS
1. 🔀 This communication is responsive to <u>8/4/03</u> .			
2. ☑ The allowed claim(s) is/are <u>1-20</u> .			
3.~igotimes The drawings filed on $ hinspace 04$ $ hinspace August 2003$ are accepted by the	e Examiner.		
4. Acknowledgment is made of a claim for foreign priority unall All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority do International Bureau (PCT Rule 17.2(a)). * Certified copies not received:	e been received. e been received in Application	No	ation from the
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		a reply complying with the re	quirements
 A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which giv 			IOTICE OF
3. CORRECTED DRAWINGS (as "replacement sheets") mus	st be submitted.		
(a) ☐ including changes required by the Notice of Draftspers	son's Patent Drawing Review	(PTO-948) attached	
1) 🗌 hereto or 2) 🔲 to Paper No./Mail Date	<u>.</u> .		
(b) including changes required by the attached Examiner Paper No./Mail Date	's Amendment / Comment or i	n the Office action of	
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t	1.84(c)) should be written on the the header according to 37 CFR	drawings in the front (not the 1.121(d).	e back) of
7. DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT			Note the
Attachment(s) 1. ☑ Notice of References Cited (PTO-892)	5 □ Notice of Info	ormal Patent Application (PT	O-152)
2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)	6. ☐ Interview Sur	mmary (PTO-413),	,
3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0	Paper No./N 08), 7. ⊠ Examiner's A	lail Date mendment/Comment	
Paper No./Mail Date <u>of</u> 4. ☐ Examiner's Comment Regarding Requirement for Deposit	8 🕅 Examiner's S	tatement of Reasons for Alle	owance
of Biological Material	9. ☐ Other		

U.S. Patent and Trademark Office PTOL-37 (Rev. 1-04) Xavi OSTa

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the change and/or additions be unaceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in an interview with Attorney, Tony M. Cole, on 6/21/04.

The application has been amended as follows:

In Claim 7, page 10, "the method of claim" should be -the method of claim 1--

REASONS FOR ALLOWANCE

- 2. Claims 1-20 are allowed.
- 3. The following is an examiner's statement of reasons for allowance: None of the references of record teaches or suggests as cited in claims 1, 9, 15: forming an etch stop layer over the fist layer; etching the etch stop layer and the first layer to form the gate electrode in the first layer in a shape corresponding to the gate pattern 9as cited in claim 1); forming a second layer over the first layer, the second layer comprising at least one of Ti and TiN; forming a third layer over the second layer, the third layer comprising an anti-reflective coating (ARC); etching the first, second and third layers to form the gate for the finFET (as cited in claim 9); a second layer over the first layer, the second layer comprising at least one of Ti and TiN; a third layer over the second layer, the third layer comprising an anti-reflective coating (ARC); wherein the first, second and third layers to form the gate for the finFET (as cited in claim 15).
- 4. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the

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issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

CONCLUSION

5. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: Fried (6,657,252 B2): FinFET CMOS with NVRAM Capability.

6. Any inquiry concerning this communication on earlier communications from the examiner should be directed to David Nhu, (571)272-1792. The examiner can normally be reached on Monday-Friday from 7:30 AM to 5:00 PM.

The examiner's supervisor, David Nelms can be reached on (571)272-1787.

The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

David Nhu

June 21, 2004

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